

N-CHANNEL ENHANCEMENT MOS FET

ABSOLUTE MAXIMUM RATINGS			
PARAMETER	SYMBOL		UNITS
Drain-Source Volt.(1)	V _{DSS}	800	V _{dc}
Drain-Gate Voltage (R _{GS} =1.0M Ω) (1)	V _{DGR}	800	V _{dc}
Gate-Source Voltage Continuous	V _{GS}	± 30	V _{dc}
Drain Current Continuous (T _c = 25°C)	I _D	9.0	A _{dc}
Drain Current Pulsed(3)	I _{DM}	36.0	A
Total Power Dissipation	PD	240	W
Power Dissipation Derating > 25°C		1.2	W/°C
Operating & Storage Temp.	T _J /T _{sig}	-55 TO +150	°C
Thermal Resistance	R _{thJc}	0.8	°C/W
Max.Lead temperature	TL	300	°C

800V, 9.0A, 1.4 Ω

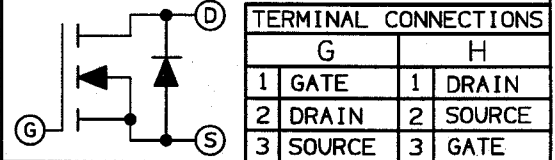
SDF9NA80 JAA
SDF9NA80 JAB

FEATURES

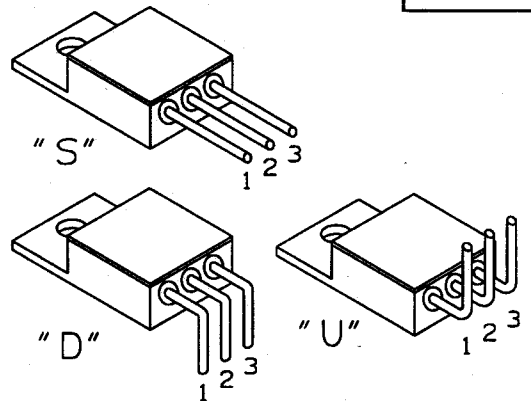
- RUGGED PACKAGE
- HI-REL CONSTRUCTION
- CERAMIC EYELETS
- LEAD BENDING OPTIONS
- COPPER CORED 52 ALLOY PINS
- LOW IR LOSSES
- LOW THERMAL RESISTANCE
- OPTIONAL MIL-S-19500 SCREENING (TX-S)

ELECTRICAL CHARACTERISTICS T _c = 25°C (UNLESS OTHERWISE SPECIFIED)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-source Breakdown Volt.	V(BR) _{DSS}	V _{GS} =0V I _D =250 μ A	800	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	V _D =V _{GS} I _D =1 MA	2.0	-	4.0	V
Gate Source Leakage	I _{GSS}	V _{GS} = ± 30 V	-	-	100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _D =MAX. RATING V _{GS} =0	-	-	250	μ A
		V _D =0.8 MAX. RATING V _{GS} =0 T _J =125°C	-	-	1000	μ A
Static Drain-Source On-State Resistance(1)	R _{DS(ON)}	V _{GS} =10V I _D =4.5A	-	-	1.4	Ω
Input Capacitance	C _{ISS}	V _{GS} =0V V _D =25 V	-	2410	-	pF
Output Capacitance	C _{OSS}	f=1.0MHz	-	370	-	pF
Reverse Transfer Capacitance	C _{RSS}		-	120	-	pF
Turn-On Delay	t _{d(on)}	V _{DD} =400V R _G =1.8 Ω I _D =9.0A V _{GS} =15V	-	-	27	ns
Rise Time	t _r	(MOSFET switching times are essentially independent of operating temp.)	-	-	36	ns
Turn-Off Delay	t _{d(off)}		-	-	94	ns
Fall Time	t _f		-	-	48	ns
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q _g	V _{GS} =15V, I _D =9.0A	-	-	88	nC
Gate-Source Charge	Q _{gs}	V _D =0.5 MAX. RATING (Gate charge is essentially independent of the operating temperature)	-	-	8.9	nC
Gate-Drain Charge (*Miller*)	Q _{gd}		-	-	44	nC

SCHEMATIC

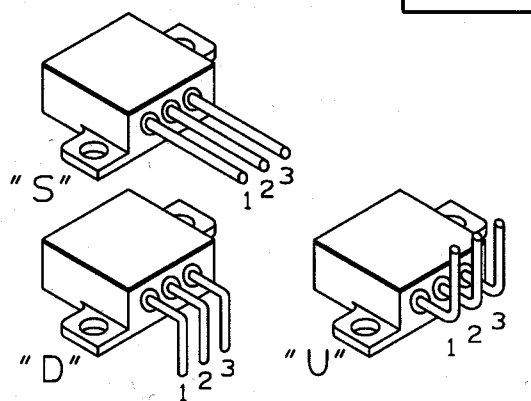


STANDARD BEND CONFIGURATIONS



(CUSTOM BEND OPTIONS AVAILABLE)

STANDARD BEND CONFIGURATIONS



(CUSTOM BEND OPTIONS AVAILABLE)

SOURCE-DRAIN DIODE RATINGS & CHARACT. T _c = 25°C (UNLESS OTHERWISE SPECIFIED)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Continuous Source Current (Body Diode)	I _S	Modified MOSFET symbol showing the integral reverse P-N junction rectifier (See schematic)	-	-	9.0	A
Pulse Source Current (Body Diode) (1)	I _{SM}		-	-	36	A
Diode Forward Voltage (2)	V _{SD}	I _F =9.0A V _{GS} =0V T _c =+25°C	-	-	1.4	V
Reverse Recovery Time	t _{rr}	T _c =+25°C	-	-	656	ns
Reverse Recovery Charge	Q _{rr}	I _F =9.0A di/dt=100A/ μ S	-	6.2	-	μ C

(1) T_J = 25°C to 150°C.
(2) Pulse test: Pulse Width < 300 μ S, Duty Cycle < 2%.
(3) Repetitive Rating: Pulse Width limited By Max. junction Temperature.